

N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
40	0.045 at V _{GS} = 10 V	3.9
	0.058 at V _{GS} = 4.5 V	3.5

FEATURES

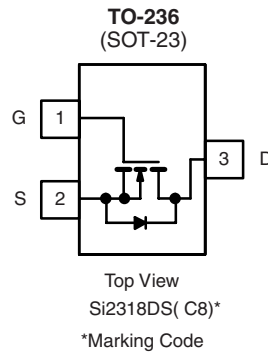
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Stepper Motors
- Load Switch



Ordering Information: Si2318DS-T1-E3 (Lead (Pb)-free)
Si2318DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	40		V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	3.9	3.0	A	
	T _A = 70 °C	3.1	2.4		
Pulsed Drain Current ^b	I _{DM}	16			
Continuous Source Current (Diode Conduction) ^{a, b}	I _S	0.8		W	
Power Dissipation ^{a, b}	T _A = 25 °C	1.25	0.75		
	T _A = 70 °C	0.8	0.48		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 5 s	75	100	°C/W	
	Steady State	120	166		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
b. Pulse width limited by maximum junction temperature

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	40			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1		3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 32\text{ V}, V_{GS} = 0\text{ V}$			0.5	μA
		$V_{DS} = 32\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 4.5\text{ V}, V_{GS} = 10\text{ V}$	6			A
Drain-Source On-Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.9\text{ A}$		0.036	0.045	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 3.5\text{ A}$		0.045	0.058	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 3.9\text{ A}$		11		S
Diode Forward Voltage	V_{SD}	$I_S = 1.25\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 3.9\text{ A}$		10	15	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			2.1		
Gate Resistance	R_g			1.8		Ω
Input Capacitance	C_{iss}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		540		pF
Output Capacitance	C_{oss}			80		
Reverse Transfer Capacitance	C_{rss}			45		
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 20\ \Omega$ $I_D \cong 1.0\text{ A}, V_{GEN} = 10\text{ V}, R_G = 6\ \Omega$		5	10	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			15	25	

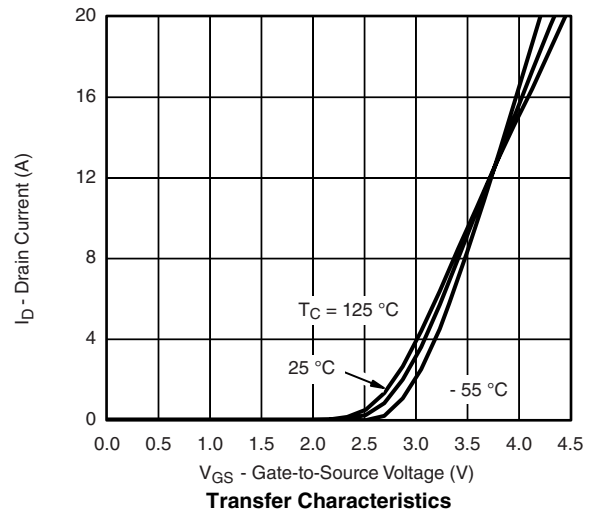
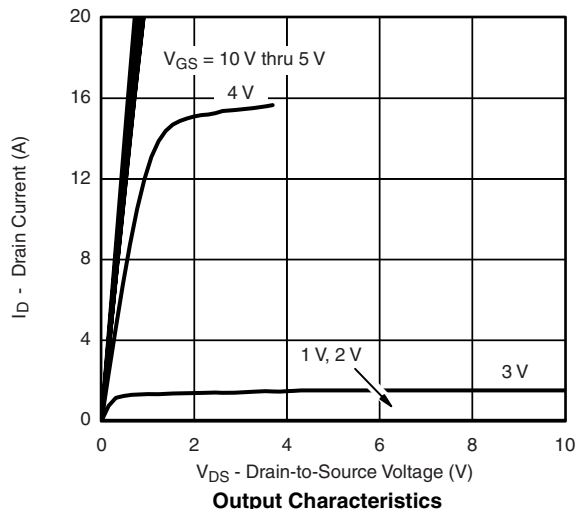
Notes:

a. Pulse test; $PW \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

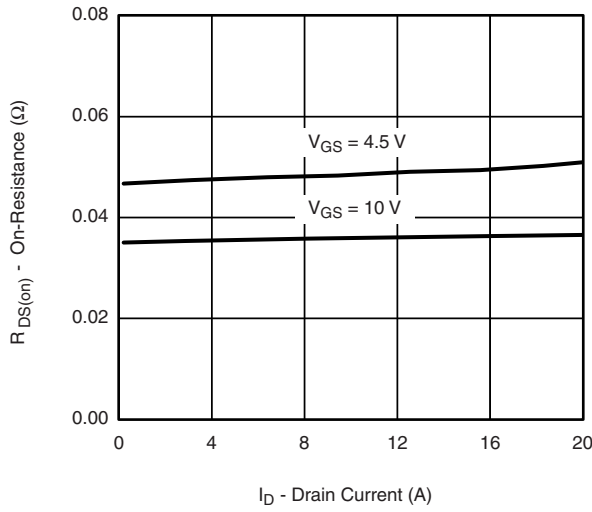
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

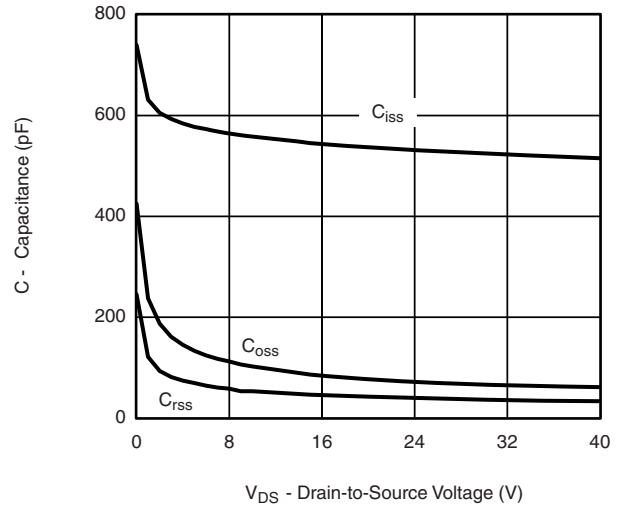
TYPICAL CHARACTERISTICS 25°C , unless otherwise noted



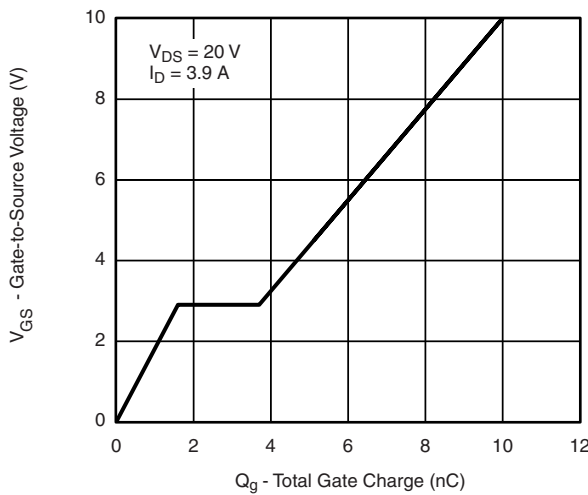
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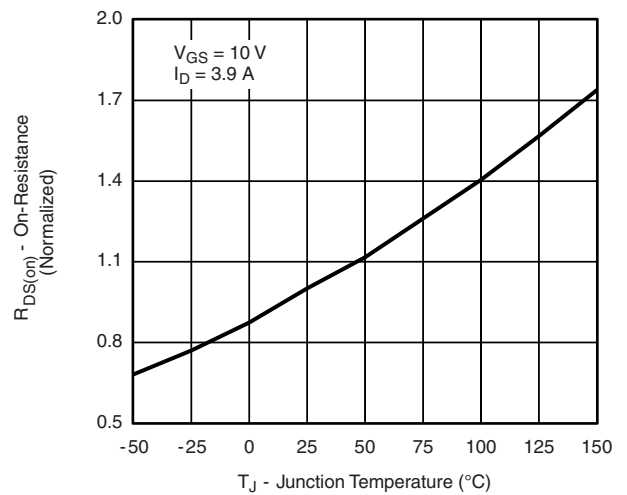
On-Resistance vs. Drain Current



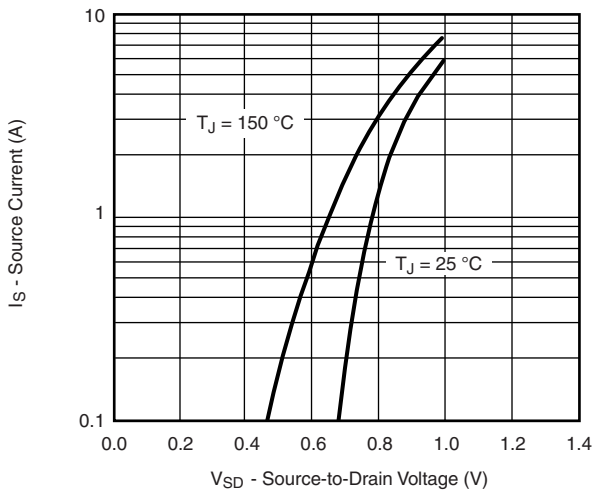
Capacitance



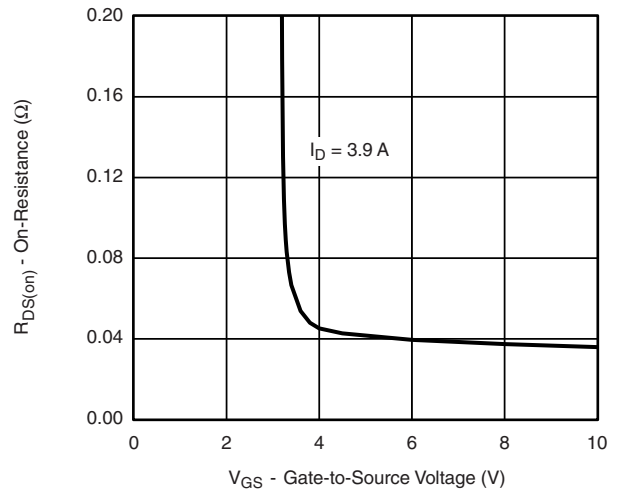
Gate Charge



On-Resistance vs. Junction Temperature

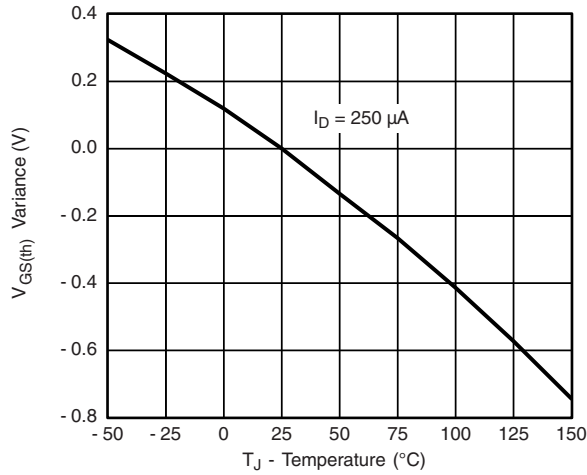


Source-Drain Diode Forward Voltage

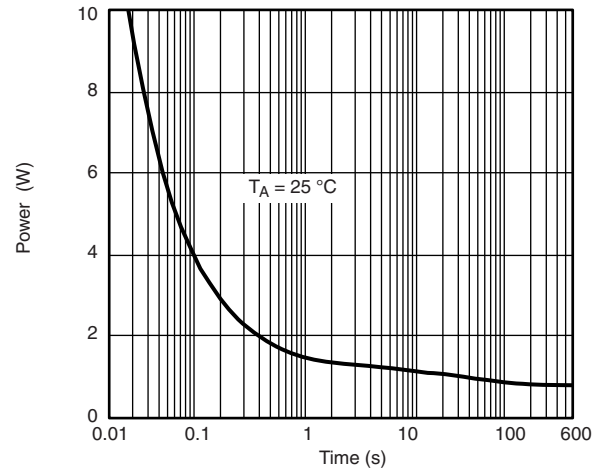


On-Resistance vs. Gate-to-Source Voltage

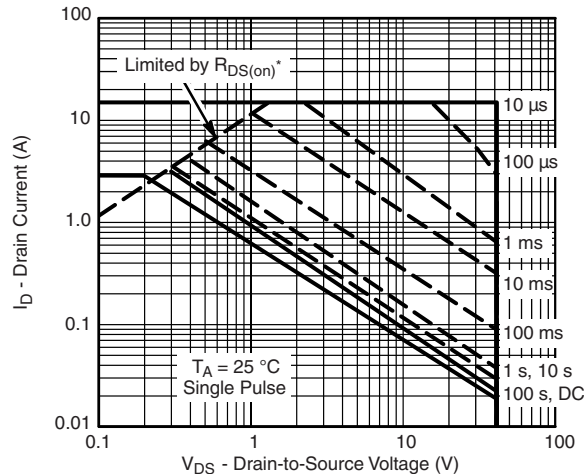
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Threshold Voltage

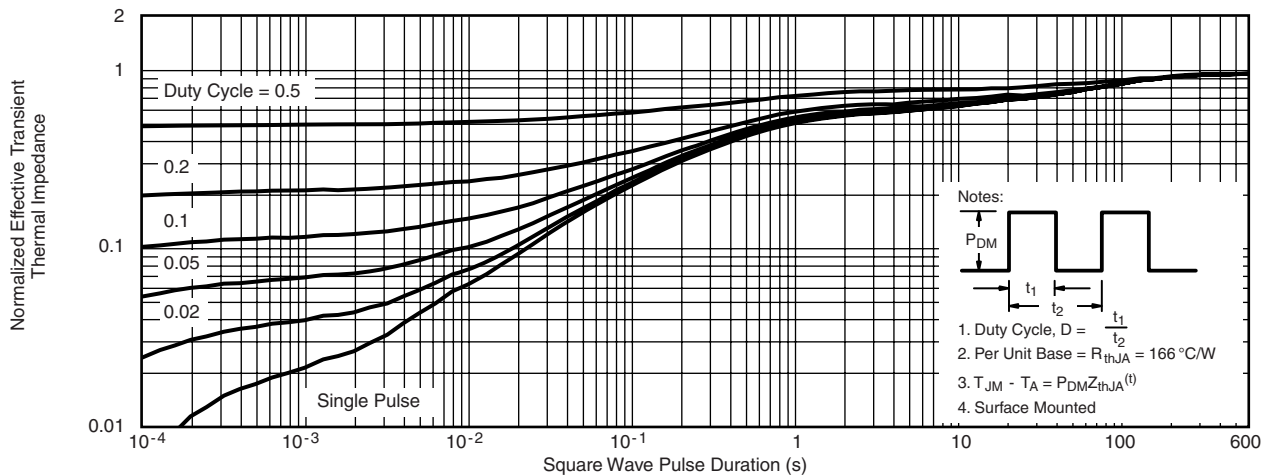


Single Pulse Power



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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